

IN THE SPECIFICATION

Please replace paragraph [0044] with the following:

W' [0044] Subsequent processing in accordance with the second method is similar to the first method. A spring metal (first) mask 340 is formed over stress-balancing layer 330 (Fig. 6(E)), and a first etchant (e.g., a Cr etch) 342 is utilized to form spring metal island 320-1, etch stop island 325-1, and stress-balancing island 330-1 (Fig. 6(F)). Subsequently, a second etchant 344 (e.g., anisotropic etching using fluorine plasma) is utilized to etch the release material layer to form a release material island 310-1 (Fig. 6(G)), and the spring metal mask is removed (Fig. 6(H)). A release mask 350 is then formed that exposes a (first) portion 330-1 of the stress-balancing layer (Fig. 6(I)), and then this first portion is removed using etchant 352 (e.g., anisotropic etching using fluorine plasma; Fig. 6(J)). An optional additional etchant 353 is then utilized, if necessary, to remove a portion 325-1A of the etch stop material from claw portion 320-1A (Figs. 6(J) and 6(K)), and then a release etchant 354 is utilized to release claw 125-A (Fig. 6(L)), which then forms a spring structure 100-A (Fig. 6(M)) having essentially the same characteristics described above with reference to Figs. 1-4, wherein a portion 325-A of the etch stop layer is formed between anchor portion 122-A of the spring metal finger and stress-balancing pad 130-A.